Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

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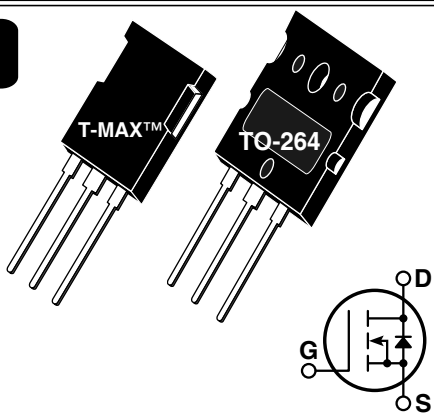
Microsemi
POWER PRODUCTS GROUP

APT34N80B2C3G
APT34N80LC3G

*G Denotes RoHS Compliant, Pb Free Terminal Finish.

800V 34A 0.145Ω

Super Junction MOSFET



COOLMOS™ Power Semiconductors

- **Ultra low $R_{DS(ON)}$**
- **Low Miller Capacitance**
- **Ultra Low Gate Charge, Q_g**
- **Avalanche Energy Rated**
- **Popular T-MAX™ or TO-264 Package**

Unless stated otherwise, Microsemi discrete MOSFETs contain a single MOSFET die. This device is made with two parallel MOSFET die. It is intended for switch-mode operation. It is not suitable for linear mode operation.

MAXIMUM RATINGS All Ratings: T_C = 25°C unless otherwise specified.

Symbol	Parameter	APT34N80B2C3G_LC3G	UNIT
V_{DSS}	Drain-Source Voltage	800	Volts
I_D	Continuous Drain Current @ T_C = 25°C	34	Amps
I_{DM}	Pulsed Drain Current ①	102	
V_{GS}	Gate-Source Voltage Continuous	±20	Volts
V_{GSM}	Gate-Source Voltage Transient	±30	
P_D	Total Power Dissipation @ T_C = 25°C	417	Watts
	Linear Derating Factor	3.33	W/°C
T_J,T_{STG}	Operating and Storage Junction Temperature Range	-55 to 150	°C
T_L	Lead Temperature: 0.063" from Case for 10 Sec.	300	
dv/dt	Drain-Source Voltage slope (V_{DS} = 640V, I_D = 34A, T_J = 125°C)	50	V/ns
I_{AR}	Repetitive Avalanche Current ⑦	17	Amps
E_{AR}	Repetitive Avalanche Energy ⑦	0.5	mJ
E_{AS}	Single Pulse Avalanche Energy ④	670	

STATIC ELECTRICAL CHARACTERISTICS

Symbol	Characteristic / Test Conditions	MIN	TYP	MAX	UNIT
BV_{DSS}	Drain-Source Breakdown Voltage (V_{GS} = 0V, I_D = 500µA)	800			Volts
$R_{DS(on)}$	Drain-Source On-State Resistance ② (V_{GS} = 10V, I_D = 22A)		0.125	0.145	Ohms
I_{DSS}	Zero Gate Voltage Drain Current (V_{DS} = 800V, V_{GS} = 0V)		1.0	50	µA
	Zero Gate Voltage Drain Current (V_{DS} = 800V, V_{GS} = 0V, T_J = 150°C)			500	
I_{GSS}	Gate-Source Leakage Current (V_{GS} = ±20V, V_{DS} = 0V)			±200	nA
$V_{GS(th)}$	Gate Threshold Voltage (V_{DS} = V_{GS}, I_D = 2mA)	2.10	3	3.9	Volts

CAUTION: These Devices are Sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.

Microsemi Website - http://www.microsemi.com

"COOLMOS™ comprise a new family of transistors developed by Infineon Technologies AG. "COOLMOS" is a trademark of Infineon Technologies AG"

050-7147 Rev G 9-2017

DYNAMIC CHARACTERISTICS

APT34N80B2C3G_LC3G

Symbol	Characteristic	Test Conditions	MIN	TYP	MAX	UNIT
C_{iss}	Input Capacitance	V_{GS} = 0V V_{DS} = 25V f = 1 MHz		4510		pF
C_{oss}	Output Capacitance			2050		
C_{rss}	Reverse Transfer Capacitance			110		
Q_g	Total Gate Charge ③	V_{GS} = 10V V_{DD} = 400V I_D = 34A @ 25°C		180	355	nC
Q_{gs}	Gate-Source Charge			22		
Q_{gd}	Gate-Drain ("Miller") Charge			90		
$t_{d(on)}$	Turn-on Delay Time	**RESISTIVE SWITCHING** V_{GS} = 10V V_{DD} = 400V I_D = 34A @ 125°C R_G = 2.5Ω		25		ns
t_r	Rise Time			15		
$t_{d(off)}$	Turn-off Delay Time			70	80	
t_f	Fall Time			6	9	
E_{on}	Turn-on Switching Energy ⑥	**INDUCTIVE SWITCHING @ 25°C** V_{DD} = 533V, V_{GS} = 15V I_D = 34A, R_G = 5Ω		675		µJ
E_{off}	Turn-off Switching Energy			580		
E_{on}	Turn-on Switching Energy ⑥	**INDUCTIVE SWITCHING @ 125°C** V_{DD} = 533V, V_{GS} = 15V I_D = 34A, R_G = 5Ω		1145		
E_{off}	Turn-off Switching Energy			670		

SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS

Symbol	Characteristic / Test Conditions	MIN	TYP	MAX	UNIT
I_S	Continuous Source Current (Body Diode)			34	Amps
I_{SM}	Pulsed Source Current ① (Body Diode)			102	
V_{SD}	Diode Forward Voltage ② (V_{GS} = 0V, I_S = -34A)		1	1.2	Volts
t_{rr}	Reverse Recovery Time (I_S = -34A, dI_S/dt = 100A/µs, V_R = 400V)		855		ns
Q_{rr}	Reverse Recovery Charge (I_S = -34A, dI_S/dt = 100A/µs, V_R = 400V)		30		µC
$^{dv}/_{dt}$	Peak Diode Recovery $^{dv}/_{dt}$ ⑤			6	V/ns

THERMAL CHARACTERISTICS

Symbol	Characteristic	MIN	TYP	MAX	UNIT
$R_{\theta JC}$	Junction to Case			.30	°C/W
$R_{\theta JA}$	Junction to Ambient			40	

① Repetitive Rating: Pulse width limited by maximum junction temperature

② Pulse Test: Pulse width < 380 µs, Duty Cycle < 2%

③ See MIL-STD-750 Method 3471

④ Starting T_j = +25°C, L = 115.92mH, R_G = 25Ω, Peak I_L = 3.4A

⑤ I_S = -34A $^{di}/_{dt}$ = 100A/µs V_R = 480V T_J = 125°C

⑥ Eon includes diode reverse recovery. See figures 18, 20.

⑦ Repetitve avalanche causes additional power losses that can be calculated as $P_{AV}=E_{AR}*f$

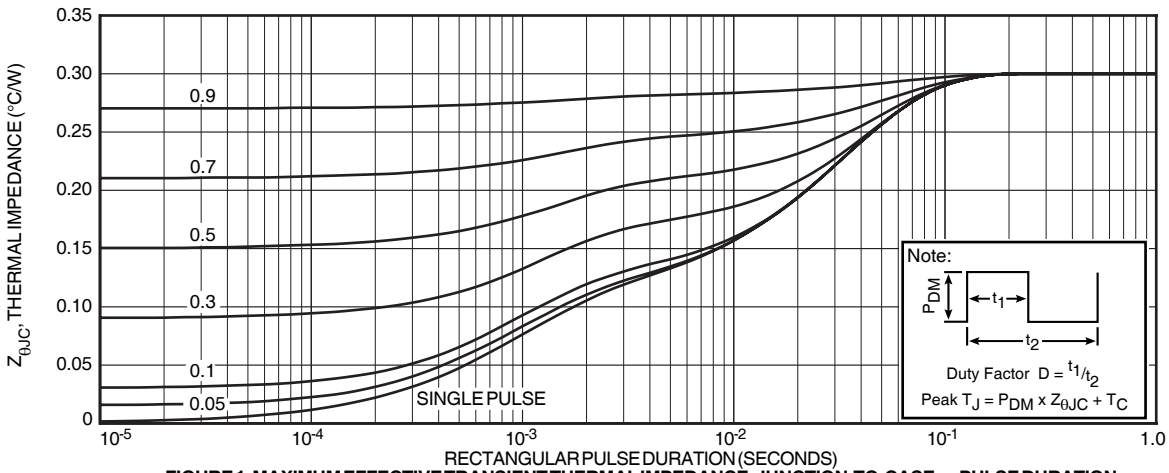


FIGURE 1, MAXIMUM EFFECTIVE TRANSIENT THERMAL IMPEDANCE, JUNCTION-TO-CASE vs PULSE DURATION

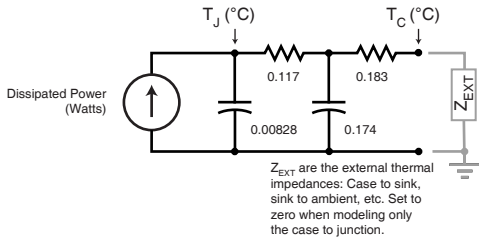


FIGURE 2, TRANSIENT THERMAL IMPEDANCE MODEL

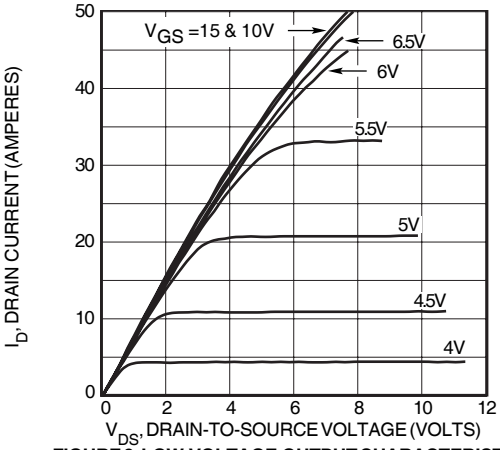


FIGURE 3, LOW VOLTAGE OUTPUT CHARACTERISTICS

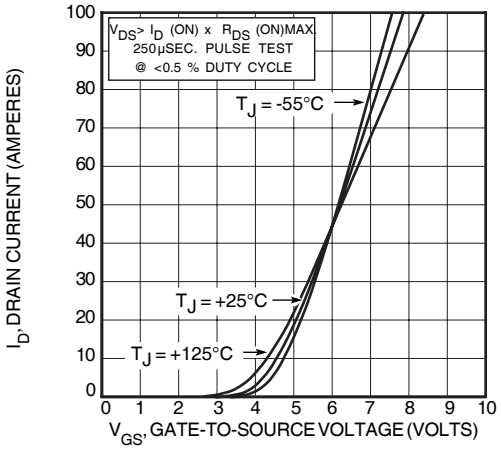


FIGURE 4, TRANSFER CHARACTERISTICS

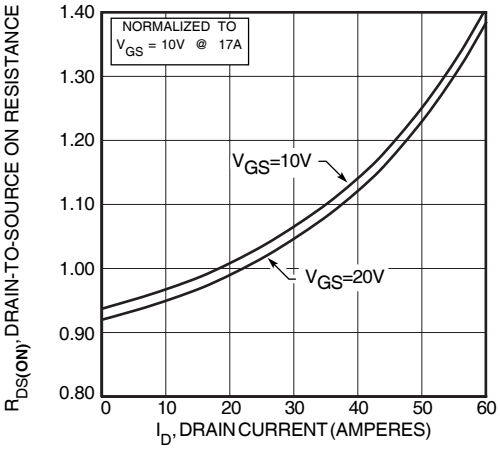


FIGURE 5, $R_{DS(ON)}$ vs DRAIN CURRENT

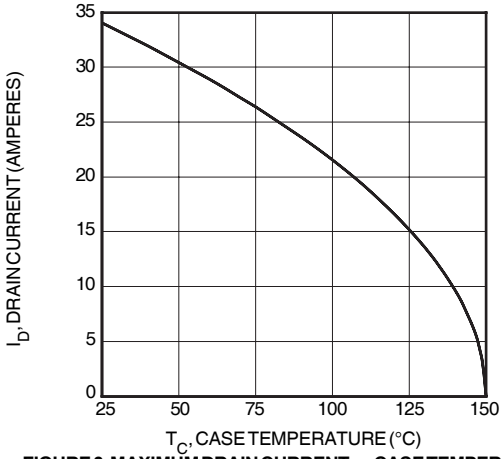


FIGURE 6, MAXIMUM DRAIN CURRENT vs CASE TEMPERATURE

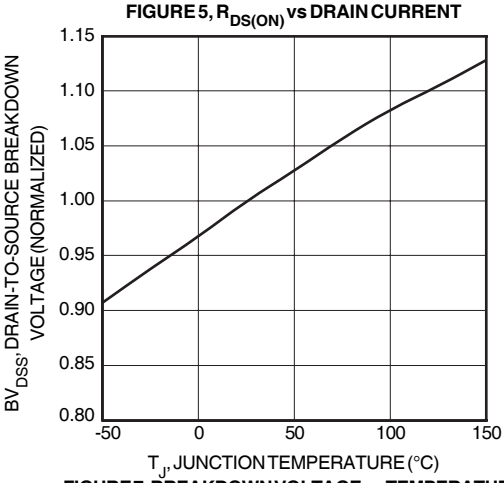


FIGURE 7, BREAKDOWN VOLTAGE vs TEMPERATURE

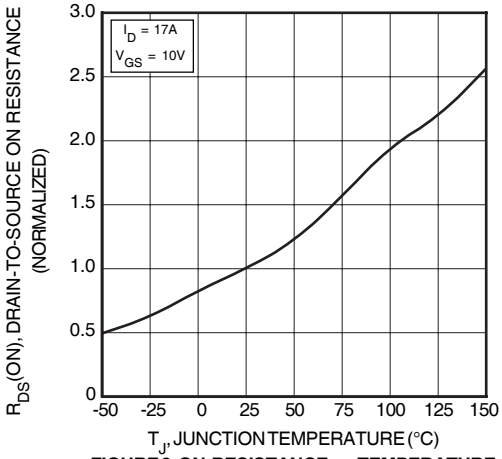


FIGURE 8, ON-RESISTANCE vs. TEMPERATURE

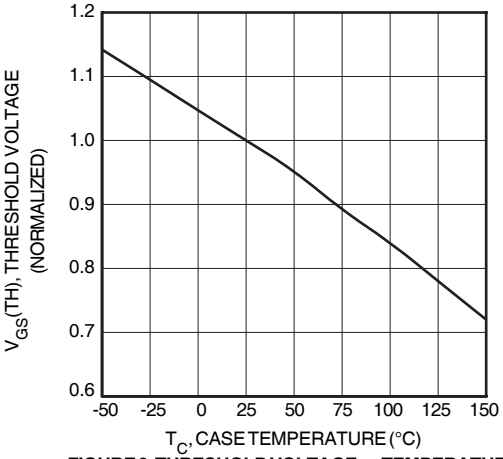


FIGURE 9, THRESHOLD VOLTAGE vs TEMPERATURE

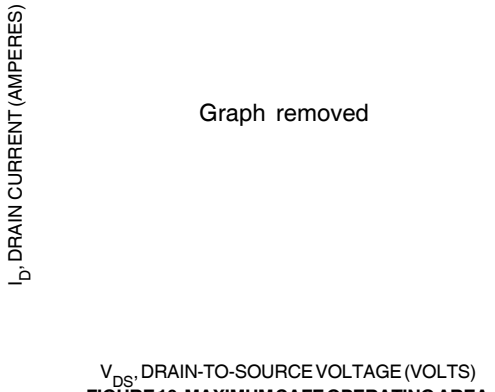


FIGURE 10, MAXIMUM SAFE OPERATING AREA

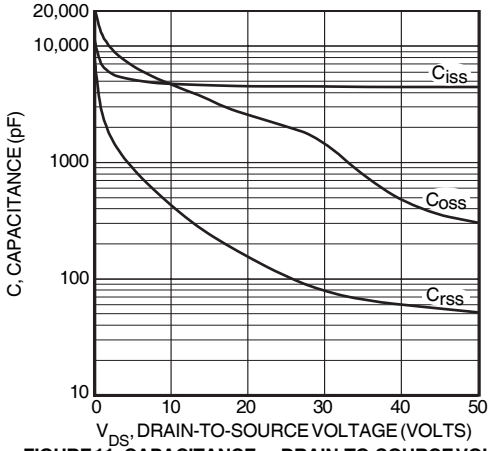


FIGURE 11, CAPACITANCE vs DRAIN-TO-SOURCE VOLTAGE

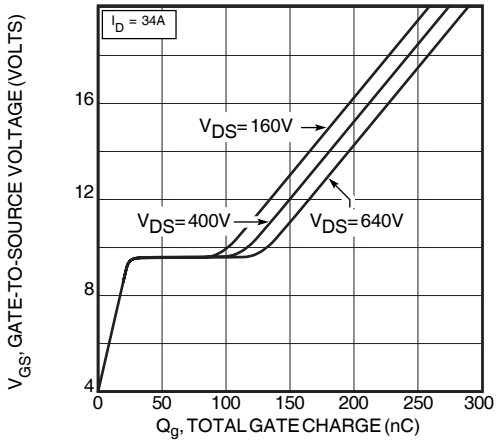


FIGURE 12, GATE CHARGES vs GATE-TO-SOURCE VOLTAGE

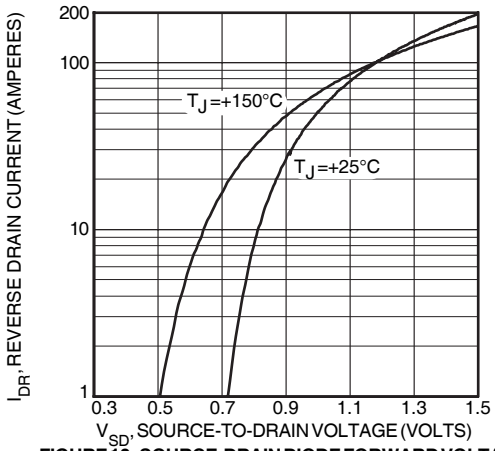


FIGURE 13, SOURCE-DRAIN DIODE FORWARD VOLTAGE

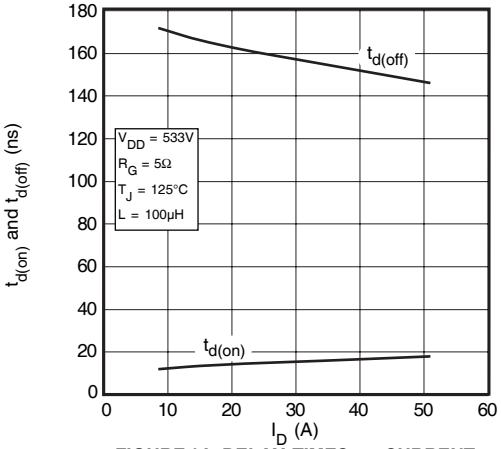


FIGURE 14, DELAY TIMES vs CURRENT

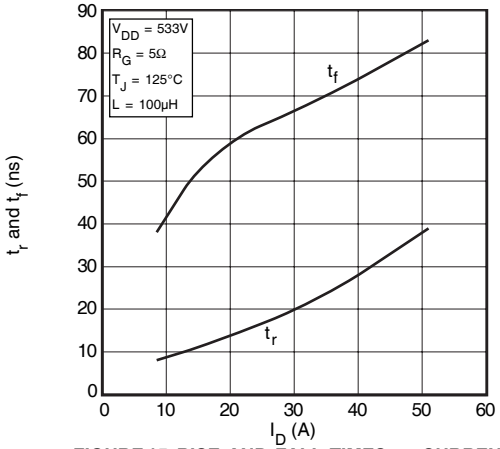


FIGURE 15, RISE AND FALL TIMES vs CURRENT

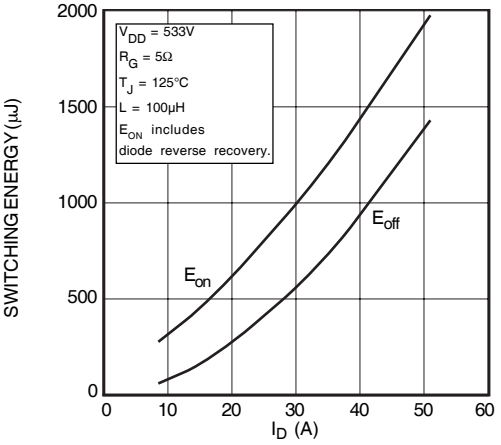


FIGURE 16, SWITCHING ENERGY vs CURRENT

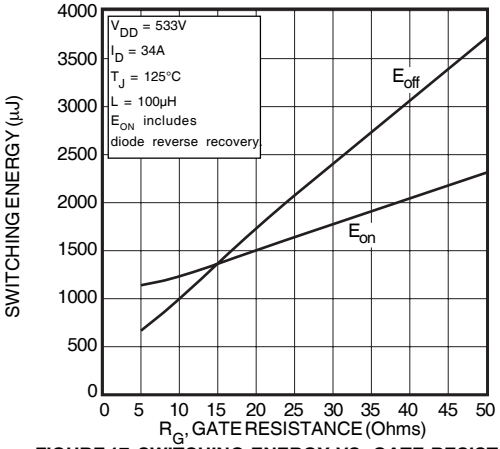


FIGURE 17, SWITCHING ENERGY VS. GATE RESISTANCE

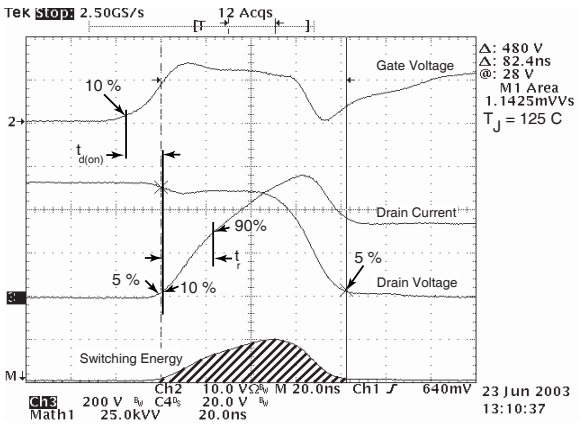


Figure 18, Turn-on Switching Waveforms and Definitions

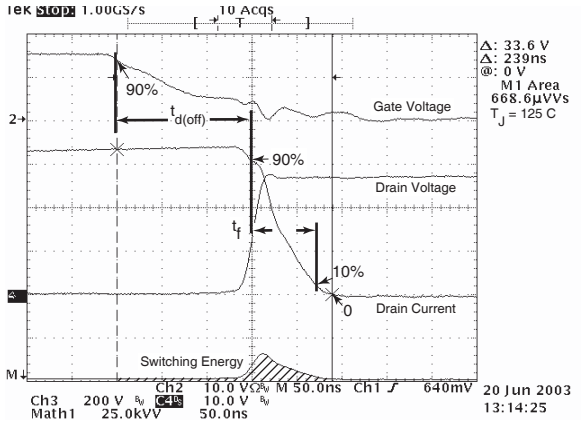


Figure 19, Turn-off Switching Waveforms and Definitions

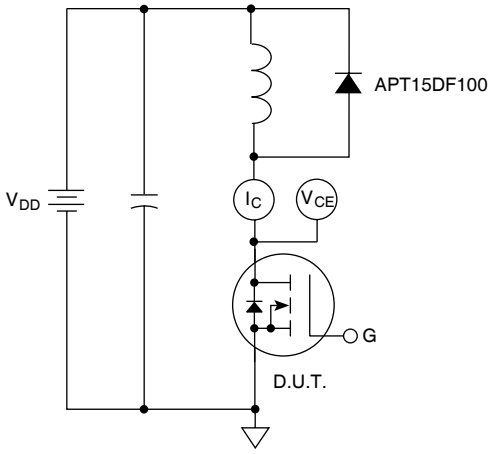
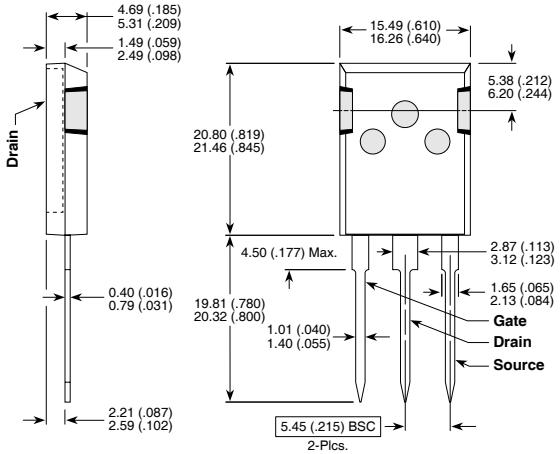


Figure 20, Inductive Switching Test Circuit

T-MAX™ (B2) Package Outline

e1 SAC: Tin, Silver, Copper

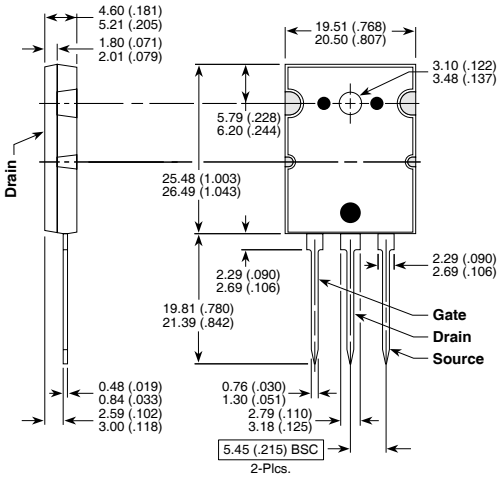


These dimensions are equal to the TO-247 without the mounting hole.

Dimensions in Millimeters and (Inches)

TO-264 (L) Package Outline

e1 SAC: Tin, Silver, Copper



Dimensions in Millimeters and (Inches)